

§Appl. No. 10/579,857
Amdt. dated January 11, 2012
Reply to Office Action of, October 11, 2011

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Cancelled)
2. (Previously Presented) The paste according to claim 18, further comprising a diluent.
3. (Previously Presented) The paste according to claim 2 wherein the diluent is butylcarbitol.
4. (Cancelled)
5. (Currently Amended) The paste according to Claim 4 18, wherein the etching agent has etching activity for antireflection layers of solar cells.
6. (Currently Amended) The paste according to Claim 4 18, wherein the etching agent has removal activity of oxidation layers and/or nitride layers of Si.
7. (Previously Presented) The paste according to Claim 18, wherein the etching agent is NH₄HF₂ or NH₄F.
8. (Cancelled)
9. (Previously Presented) The paste according to Claim 18, wherein the binder contains a thermosetting resin.

§Appl. No. 10/579,857
Amdt. dated January 11, 2012
Reply to Office Action of, October 11, 2011

10. (Previously Presented) The paste according to claim 9, wherein the thermosetting resin is an epoxy resin and/or phenol resin.

11. (Previously Presented) The paste according to Claim 18, wherein the organic solvent is polyhydric alcohol or its mixture.

12. (Previously Presented) The paste according to claim 11, wherein the polyhydric alcohol is glycerin and/or ethylene glycol.

13. (Withdrawn) A solar cell comprising a semiconductor layer, an antireflection layer above the semiconductor layer, and a surface electrode which penetrates through the antireflection layer to bring the semiconductor layer into conduction, wherein the solar cell is fabricated by coating and baking the paste according to claim 18 on the antireflection layer in a desired electrode shape.

14. (Withdrawn) An electric circuit formed by coating and baking the paste according to claim 18, on a substrate in a desired pattern.

15. (Withdrawn) A method of fabricating a solar cell comprising a semiconductor layer, an antireflection layer above the semiconductor layer, and a surface electrode which penetrates through the antireflection layer to bring the semiconductor layer into conduction, wherein the method comprises coating and baking the paste according to claim 18, on the antireflection layer in a desired electrode shape.

16. (Withdrawn) A method of forming electric circuits, which comprises coating and baking the paste according to claim 18, on a substrate in a desired pattern.

17. (Cancelled)

§Appl. No. 10/579,857

Amdt. dated January 11, 2012

Reply to Office Action of, October 11, 2011

18. (Previously Presented) A functional paste comprising 60-99 wt% of a metal powder, 0.1 – 20 wt.% of an etching agent, 0.1 – 30 wt.% of a binder and 0.1 – 30 wt.% of an organic solvent, and 0.1 – 5.0 wt.% unsaturated fatty acid,

wherein the metal powder is one or more of Ag-coated Ni powder, Cu powder, Ag powder, Au powder, or Pd powder, and

wherein the etching agent has removal activity of oxidation layers on the surfaces of metal powders, or has etching activity for antireflection layers of solar cells, or has removal activity of oxidation layers and/or silicon nitride layers.

19. (Currently Amended) A functional paste according to claim ~~47~~ 18, wherein the unsaturated fatty acid is oleic acid or linoleic acid.

20. (Cancelled)